Data Sheet

AEC-Q101 Qualified

Schottky Barrier Diodes

RB160VA-40FH

●Applications

General rectification

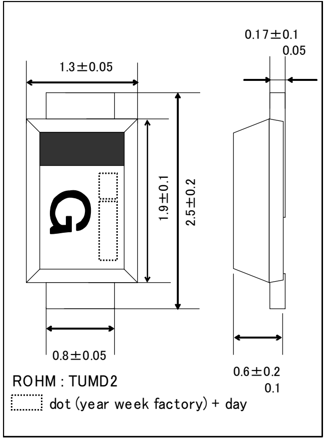
●Features

1) Small mold type. (TUMD2)
2) Low V_F, Low I_R.
3) High reliability.

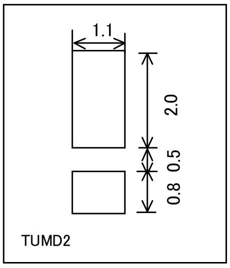
●Construction

Silicon epitaxial planar

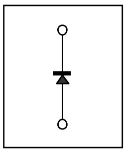
●Dimensions (Unit : mm)



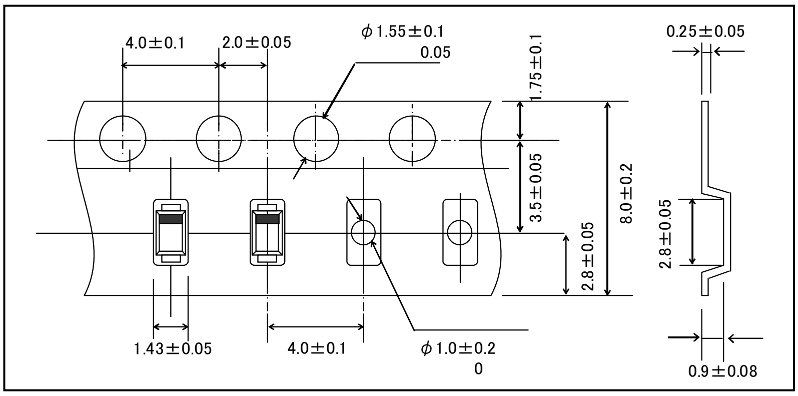
● Land size figure (Unit : mm)



●Structure



● Taping specifications (Unit : mm)



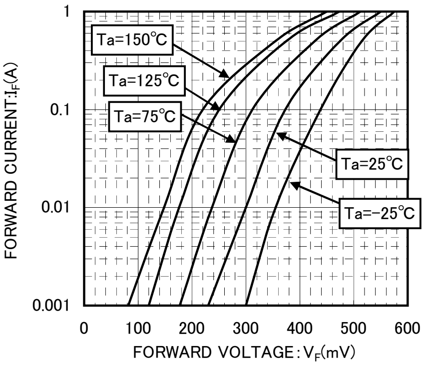
●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive)	V_{RM}	40	V
Reverse voltage (DC)	V_R	40	V
Average rectified forward current	Io	1	A
Forward current surge peak（60Hz･1cyc）	I_{FSM}	5	A
Forward current surge peak（t=100μs･1cyc）	I_{FSM}	10	A
Junction temperature	Tj	150	℃
Storage temperature	Tstg	-40 to +150	℃

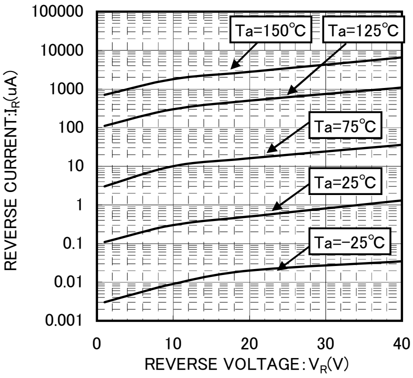
●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	0.50	0.55	V	I_F=700mA
Reverse current	I_R	-	1.5	50	μA	V_R=40V

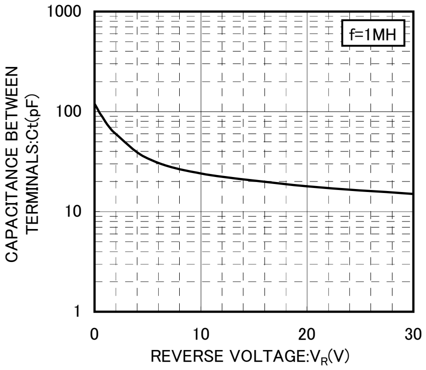
●Electrical characteristic curves (Ta=25°C)



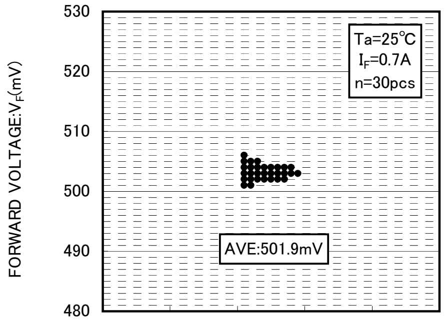
V_F-I_F CHARACTERISTICS



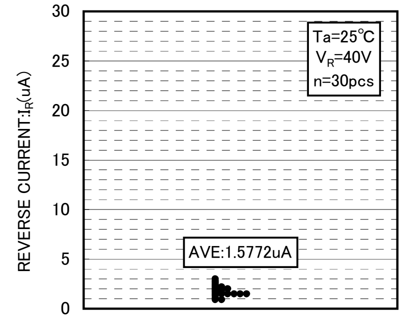
V_R-I_R CHARACTERISTICS



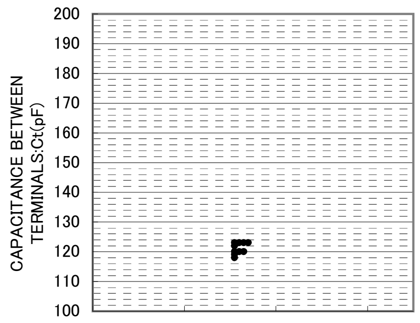
V_R-Ct CHARACTERISTICS



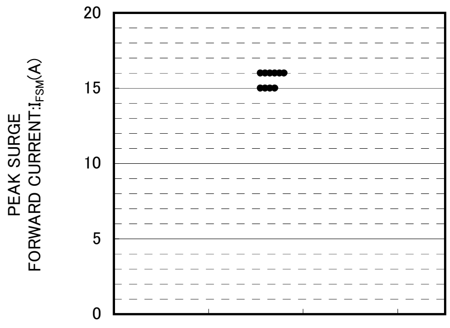
V_F DISPERSION MAP



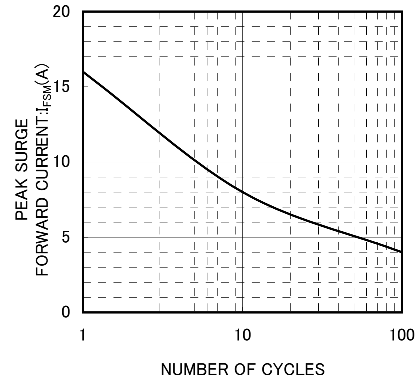
I_R DISPERSION MAP



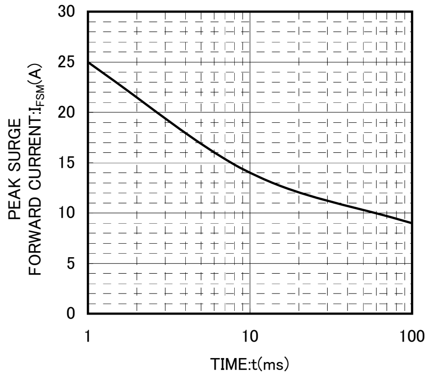
Ct DISPERSION MAP



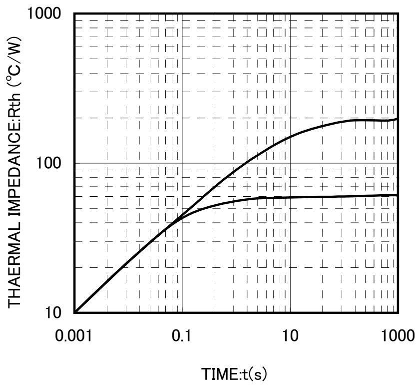
I_{FSM} DISRESION MAP



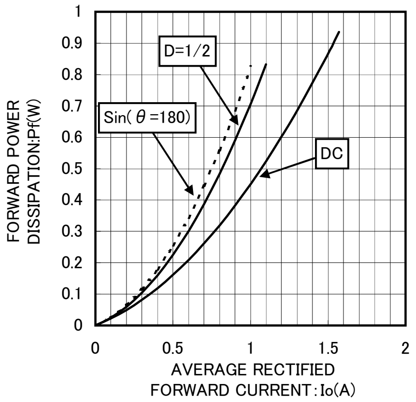
I_{FSM}-CYCLE CHARACTERISTICS



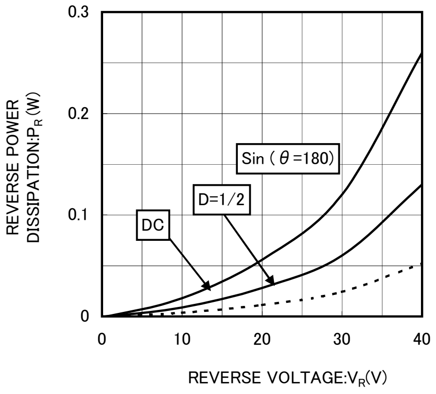
I_{FSM}-t CHARACTERISTICS



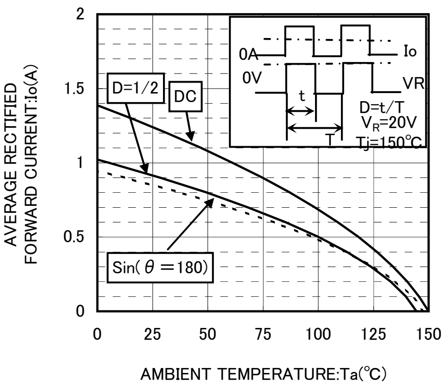
Rth-t CHARACTERISTICS



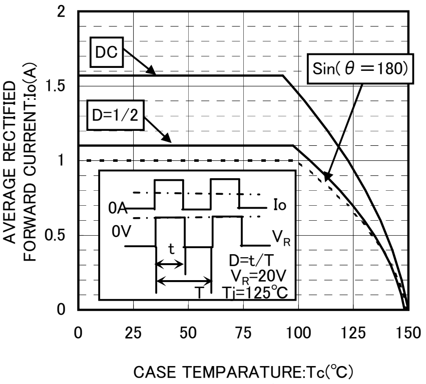
Io-Pf CHARACTERISTICS



V_R-P_R CHARACTERISTICS



Derating Curve*(Io-Ta)



Derating Curve*(Io-Tc)